

IN THE CLAIMS

Please cancel claims 6, 9 and 11 without prejudices and amend the claims as follows:

1. (Twice Amended) A shallow trench isolation in a substrate, said shallow trench isolation structure comprising:

a trench in said substrate; [and]

a nitride liner recessed within said trench and the nitride liner forming a partially enclosed volume, said partially enclosed volume being completely filled with a dielectric material which also completely fills the trench, such that an uppermost surface of said nitride liner is disposed below a transistor channel depth of a transistor disposed in a well beside said shallow trench isolation structure[.]; and

an oxide fill disposed above said nitride liner such that said oxide fill extends above the uppermost surface of said nitride liner to substantially a top surface of said substrate, such that substantially no polysilicon material is disposed within the trench.

In claim 7, line 1, change "6" to -- 1 --.

8. (Twice Amended) A shallow trench isolation in a substrate, said shallow trench isolation structure comprising:

a trench in the substrate;

a nitride liner recessed within said trench such that an uppermost surface of said nitride liner is below a channel depth, said channel depth being representative of a width of a channel associated with a device disposed beside said trench; [and]

an oxide fill disposed above said nitride liner, such that said oxide fill extends above and below [an] the uppermost surface of said nitride liner substantially to a top surface of said substrate and completely filling below the uppermost surface, respectively[.]; and

the oxide fill is disposed above said liner such that substantially no polysilicon material is disposed within the trench.